CLAIM

What is claimed is:

1. An improved processing method for the packaging technique of a large size FED comprising the steps of:

providing an ITO conducting glass;

forming a BM layer area, a multi-phosphor layer area and a hollow area on an ITO conducting glass using the first screen mask and the second screen mask, and forming a Cr/CrO_x layer area in the hollow area;

forming an Al layer on said areas, then carrying out a sintering process of phosphor layer to form an AlO_x layer;

fixing a spacer on the hollow area of the AlO_x layer; and

aligning process for a lower plate.

2. An improved packaging technique of a large size FED of claim 1, wherein the method of forming an Al layer is an evaporation, the thickness is about 1000-3000 angstroms.

3. An improved packaging technique of a large size FED of claim 1, wherein the temperatures of the sintering process of the phosphor layer is about 500-560 ℃.

4. An improved packaging technique of a large size FED of claim 1, wherein the thickness of the AlO_x layer is around 50-200 angstroms.

5. An improved packaging technique of a large size FED of claim 1, wherein the thickness of the Cr/CrO_x layer is around 1000-3000 angstroms.

6. An improved packaging technique of a large size FED of claim 1, wherein the spacer is form as a column structure, and the height of the spacer is about 1.1 mm.

7. An improved packaging technique of a large size FED of claim 1, wherein there is a plurality of bonding areas between the spacer and the AlO_x layer.

8. An improved packaging technique of a large size FED of claim 1, wherein said method of fixing the spacer is an anodic bonding technique.

9. An improved packaging technique of a large size FED of claim 1, wherein the voltage of fixing the spacer is 1.00-1.50 V/μm.

10. An improved packaging technique of a large size FED of claim 1, wherein the temperature of fixing the substrate glass of the spacer is 200-300 ℃.

11. An improved structure for the packaging technique of a large size FED comprising of:

an ITO conducting glass;

on the ITO conducting glass is defined to a BM layer area, a multi-phosphor layer area, and a hollow area, in which the inside of a hollow area is formed a Cr/CrO_x layer area;

said areas are coated with an Al layer;

an Al layer is coated with an AlO_x layer;

a spacer is fixed on an AlO_x layer of the hollow area; and

a lower plate is fixed on the spacer.

12. An improved packaging technique of a large size FED of

claim11, wherein said method of forming an Al layer is an evaporation, and the thickness is around 1000-3000 angstroms.

13. An improved packaging technique of a large size FED of claim11, wherein the temperature of the sintering process of the phosphor layer is around 500-560 ℃.

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14. An improved packaging technique of a large size FED of claim 11, wherein the thickness of the AlO_x layer is around 50-200 angstroms.

15. An improved packaging technique of a large size FED of claim 11, wherein said the thickness of the Cr/CrO_x layer is around 1000-3000 angstroms.

16. An improved packaging technique of a large size FED of claim 11, wherein said spacer is form as a column structure, and the height of the spacer is about 1.1 mm.

17. An improved packaging technique of a large size FED of claim 11, wherein there is a plurality of bonding areas between the spacer and an AlO_x layer.

18. An improved packaging technique of a large size FED of claim 11, wherein said method of fixing the spacer is an anodic bonding technique.

19. An improved packaging technique of a large size FED of claim 11, wherein the voltage of fixing the spacer is 1.00-1.50 V/μm.

20. An improved packaging technique of a large size FED of claim 11, wherein the temperature of fixing the substrate glass of the spacer is 200-300 ℃.